

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	238	438/535.ccls.	US-PGPUB; USPAT	OR	ON	2009/02/18 12:31
L2	238	438/535.ccls.	US-PGPUB; USPAT	OR	ON	2009/02/18 12:31
L3	167	257/E21.135.ccls.	US-PGPUB; USPAT	OR	ON	2009/02/18 12:39
L4	5	((oxid\$5 with (remov\$3 or etch\$3)) and (dip\$4 or wet\$4 or submerg\$3 or plac\$3) and (liquid or solution) and (adipic adj acid)).CLM.	US-PGPUB	OR	ON	2009/02/18 13:32
L5	229	257/E21.143.ccls.	US-PGPUB; USPAT	OR	ON	2009/02/18 13:34
S1	2	("5387545"   "5851906").FN.	US-PGPUB; USPAT	OR	ON	2007/07/01 16:27
S2	2	silicon and (native with oxide with removal with scrubbing)	USPAT	OR	ON	2007/07/01 16:32
S3	592	electromagnetic with dop\$3	USPAT	OR	ON	2007/07/02 10:49
S4	0	S3 and (energy with (Kj or kilojoule))	USPAT	OR	ON	2007/07/01 16:33
S5	0	S3 and (energy with (Kj or kilo\$joule))	USPAT	OR	ON	2007/07/01 16:33
S6	10	S3 and (energy with joule)	USPAT	OR	ON	2007/07/01 16:33
S7	3	S3 and (binding with energy)	USPAT	OR	ON	2007/07/01 16:36
S8	21	(electromagnetic with dop\$3) and energy and joule	USPAT	OR	ON	2007/07/02 10:51
S9	0	electromagnetic adj dop \$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/02 10:52

S10	0	electromagnetic adj wave adj dop\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/02 10:52
S11	238	(electromagnetic adj wave) with dop\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/02 16:30
S12	217	438/535.cols.	US-PGPUB; USPAT	OR	ON	2007/07/02 16:32
S13	6	S12 and (native with oxide)	US-PGPUB; USPAT	OR	ON	2007/07/02 16:32
S14	6	("5599735").URPN.	USPAT	OR	ON	2007/07/02 16:55
S15	2597	((gas with phase with dop\$3) or GPD)	USPAT	OR	ON	2007/07/02 16:55
S16	250	gas adj phase adj dop \$3	USPAT	OR	ON	2007/07/02 16:56
S17	43	S16 and (native with oxide)	USPAT	OR	ON	2007/07/02 16:56
S18	217	438/535.cols.	US-PGPUB; USPAT	OR	ON	2007/07/03 17:58
S19	2	semiconductor and (dip \$4 with cleann\$3 with solution)	USPAT	OR	ON	2007/12/19 11:40
S20	43	semiconductor with (scrubb\$3 or rubb\$3 or polish\$3) with ((sodium adj hydroxide) or (sulfinic adj acid) or (adipic adj acid))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/21 17:24
S21	25	semiconductor with (scrubb\$3 or rubb\$3 or clean\$3 or dipp\$3) with ((sodium adj hydroxide) or (sulfinic adj acid) or (adipic adj acid))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/21 17:28
S22	22	semiconductor with (scrubb\$3 or rubb\$3 or clean\$3 or dipp\$3) with ((sodium adj hydroxide) or (sulfinic adj acid))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 13:44

S23	1	semiconductor with (scrubb\$3 or rubb\$3) with ((sodium adj hydroxide) or (sulfinic adj acid))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 13:45
S24	0	semiconductor with (scrubb\$3 or rubb\$3 or clean\$3 or dipp\$3) with (sulfinic adj acid)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 14:03
S25	8	semiconductor with (scrubb\$3 or rubb\$3 or clean\$3 or dipp\$3) and (sulfinic adj acid)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 14:03
S26	383	semiconductor and (scrubb\$3 or rubb\$3) and (sulfinic adj acid)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 14:07
S27	85	wafer and (scrubb\$3 or rubb\$3) and (sulfinic adj acid)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 14:08
S28	0	wafer and (scrubb\$3 or rubb\$3) and (adipic adj acid adj di\$2 \$ethylhexyl adj ester)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 14:11
S29	1	(scrubb\$3 or rubb\$3 and clean\$3) and (adipic adj acid adj di\$2 \$ethylhexyl adj ester)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 14:12
S30	3	(scrubb\$3 or rubb\$3 or brush\$3) and (adipic adj acid adj di\$2 \$ethylhexyl adj ester)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:09

S31	1	S30 and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:10
S32	0	wafer and ((scrubb\$3 or rubb\$3 or clean\$3) with (sulfinic adj acid))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:16
S33	20	(wafer or semiconductor) and ((scrubb\$3 or rubb\$3 or brush\$3 or clean\$3 or dip\$4) with (sulfinic adj acid))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:17
S34	81	((scrubb\$3 or rubb\$3 or brush\$3 or clean\$3 or dip\$4) with (sulfinic adj acid))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:20
S35	40	((scrubb\$3 or rubb\$3 or brush\$3 or clean\$3) with (sulfinic adj acid))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:20
S36	0	(wafer or semiconductor) and ((scrubb\$3 or rubb\$3 or brush\$3 or clean\$3 or dipping) with (sulfinic adj acid))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:25
S37	0	semiconductor and ((scrubb\$3 or rubb\$3 or brush\$3 or clean\$3 or dipping) with (sulfinic adj acid))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:26
S38	40	((scrubb\$3 or rubb\$3 or brush\$3 or clean\$3 or dipping) with (sulfinic adj acid))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:26

S39	0	((scrub\$4 or rub\$3 or brush\$3 or clean\$3 or dipping) with (sulfinic adj acid)) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:30
S40	8	cleaning with (sulfinic adj acid)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:31
S41	1	reductive with liquid with (sulfinic adj acid)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:35
S42	3	(reductive with liquid) and (sulfinic adj acid)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:36
S43	1	(reductive adj liquid) and (sulfinic adj acid)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:38
S44	4	(reductive with clean \$3) and (sulfinic adj acid)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:45
S45	306	((reductive or reducing with liquid) and (sulfinic adj acid)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:47
S46	5	((reductive or reducing) adj liquid) and (sulfinic adj acid)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:47

S47	3	(scrubb\$3 or rubb\$3 or brush\$3 and dipping) and (adipic adj acid adj di\$2\$ethylhexyl adj ester)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:50
S48	2	(cleaning or dipping or washing) and (adipic adj acid adj di\$2\$ethylhexyl adj ester)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:52
S49	901	((reductive or reducing) adj agent) with (sulfinic adj acid)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:53
S50	25	S49 and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/29 15:53

2/18/2009 1:40:15 PM

C:\Documents and Settings\asarkar\My Documents\EAST\Workspaces\10-526999.wsp